

AMENDMENTS TO THE CLAIMS

Claims 1-10 (Canceled)

11. **(Original)** A system for processing a semiconductor wafer with a gas having a chemical component, comprising:
 - a. a first enclosure defining a first chamber for receiving the semiconductor wafer and the gas; and
 - b. a scrubber comprising:
 - i. a second enclosure defining a second chamber for receiving at least a portion of the gas from said first chamber, said second enclosure having a gas inlet in fluid communication with said first chamber and said second chamber and a gas outlet in fluid communication with said second chamber; and
 - ii. at least one substrate contained within said second chamber and located between said gas inlet and said gas outlet, said substrate having a film deposition surface for receiving a film composed of the chemical component of the gas.
12. **(Original)** A system according to claim 11, further comprising a pump located between said first chamber and said second chamber for pumping the gas from said first chamber to said second chamber via said gas inlet.
13. **(Original)** A system according to claim 11, further comprising a heating element for heating at least one of said second enclosure and said at least one substrate.
14. **(Original)** A system according to claim 11, further comprising an abatement device for removing at least one component of the exhaust gas not deposited on said substrate.

Claims 15-18 (Canceled)

19. **(Original)** A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a first chemical component and a second chemical component, comprising the steps of:
 - a. flowing the exhaust gas through an enclosure defining a chamber and containing at least one substrate; and
 - b. causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
20. **(Original)** A method according to claim 19, further comprising the step of removing the second chemical component from the exhaust gas after performing step b).
21. **(Original)** A method according to claim 19, wherein step b) is performed by heating at least one of said at least one substrate and said enclosure to at least 800°C.
22. **(Original)** A method according to claim 21, wherein step b) is performed by heating at least one of said at least one substrate and said enclosure to at least 1100°C.
23. **(Original)** A method according to claim 19, wherein the first chemical component is non-toxic and the second chemical component is toxic.
24. **(Original)** A method according to claim 23, wherein the first chemical component comprises silicon and the second chemical component comprises arsenic.
25. **(Original)** A method according to claim 19, further comprising after step b) the steps of:
 - a. removing said at least one substrate from said enclosure;
 - b. cleaning said at least one substrate of any film deposited thereon;
 - c. installing said at least one substrate in said enclosure; and
 - d. again causing the first chemical component to be chemical vapor deposited onto said at least one substrate.

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